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## Erratum

# Erratum to “Electrical Characterization of Postmetal Annealed Ultrathin TiN Gate Electrodes in Si MOS Capacitors”

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In the article titled “Electrical Characterization of Postmetal Annealed Ultrathin TiN Gate Electrodes in Si MOS Capacitors” [1], there was an error in reference [14] which should be corrected as follows:

“[14] Z. N. Khan, S. Ahmed, and M. Ali, “Effect of thermal budget on the electrical characterization of atomic layer deposited HfSiO/TiN gate stack MOSCAP structure,” *PLoS ONE*, vol. 11, no. 8, Article ID e0161736, 2016.”

## References

- [1] Z. N. Khan, S. Ahmed, and M. Ali, “Electrical characterization of postmetal annealed ultrathin TiN gate electrodes in Si MOS capacitors,” *Advances in Materials Science and Engineering*, vol. 2016, Article ID 3740517, 4 pages, 2016.



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